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List of Publications

1. **Chourasia, Nitesh K.**, Anand Sharma, Vishwas Acharya, Nila Pal, Sajal Biring, and Bhola N. Pal. "Solution processed low band gap ion-conducting gate dielectric for low voltage metal oxide transistor." **Journal of Alloys and Compounds**, vol. 777 (2019): 1124-1132.
2. **Chourasia, Nitesh K.**, Anand Sharma, Nila Pal, Sajal Biring, and Bhola N. Pal. " Dielectric/semiconductor interfacial p-doping: a new technique to fabricate solution processed high performance 1 V ambipolar oxide-transistor" **Physica status solidi (RRL)** (2020): DOI: 10.1002/pssr.202000268
3. **Chourasia, Nitesh K.**, Vijay K. Singh, Anand Sharma, Anchal Srivastava, and Bhola N. Pal." Lithography-free fabrication of low operating voltage and large channel length graphene transistor with current saturation by utilizing Li⁺ of ion-conducting-oxide gate dielectric."
4. **Chourasia, Nitesh K.**, Abhishek Kumar Singh, Suyash Rai, Anand Sharma, P. Chakrabarti, Anchal Srivastava, and Bhola N. Pal. " A Lithography Free Fabrication of Low Operating Voltage Driven, Very Large Channel Length Graphene Field Effect Transistor with NH₃ Sensing Application." **IEEE Transactions on Electron Devices**, *minor revision submitted*.
5. Abhishek Kumar Singh, **Chourasia, Nitesh K.**, Bhola N. Pal, A. Pandey and P. Chakrabarti. " Low Operating Voltage Solution Processed (Li₂ZnO₂) Dielectric and (SnO₂) Channel Based Medium Wave UV-B Phototransistor for Application in Phototherapy." **IEEE Transactions on Electron Devices**, vol. 67 (2020): 2028-2034.
6. Anand Sharma, **Chourasia, Nitesh K.**, Anumol Sugathan, Yogesh Kumar, Satyabrata Jit, Shun-Wei Liu, Anshu Pandey, Sajal Biring, and Bhola N. Pal. "Solution processed Li₅ AlO₄ dielectric for low voltage transistor fabrication and its application in metal oxide/quantum dot heterojunction phototransistors." **Journal of Materials Chemistry C**, vol. 6 (2018): 790-798.
7. Anand Sharma, **Chourasia, Nitesh K.**, Nila Pal, Shun-Wei Liu, Sajal Biring, and Bhola N. Pal. " Ultra-low Voltage Metal Oxide Thin Film Transistor by Low-temperature Annealed Solution-processed Ion-conducting Gate Dielectric **Electronic Materials Letters**, vol. 16 (2020): 22-34.
8. Anand Sharma, **Chourasia, Nitesh K.**, Nila Pal, Sajal Biring, and Bhola N. Pal. " Role of Electron Donation of TiO₂ Gate Interface for Developing Solution-processed High-performance One-volt Metal Oxide Thin Film Transistor Using Ion-conducting Gate Dielectric" **The Journal of Physical Chemistry C**, vol. 123 (2019): 20278-20286.
9. Nila Pal, Anand Sharma, Vishwas Acharya, **Chourasia, Nitesh K.**, Sajal Biring, and Bhola N. Pal. " Gate interface engineering for subvolt metal oxide transistor fabrication by using ionconducting dielectric with Mn₂O₃ gate interface." **ACS Applied Electronic Materials**, vol. 2 (2019): 25-34.

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